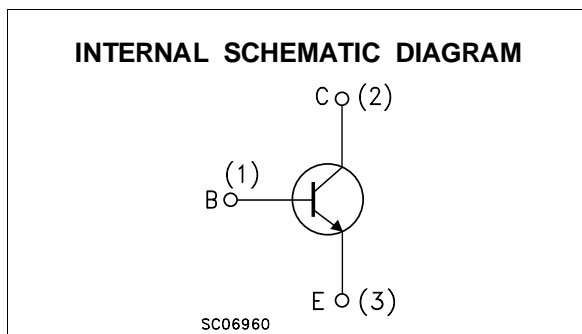
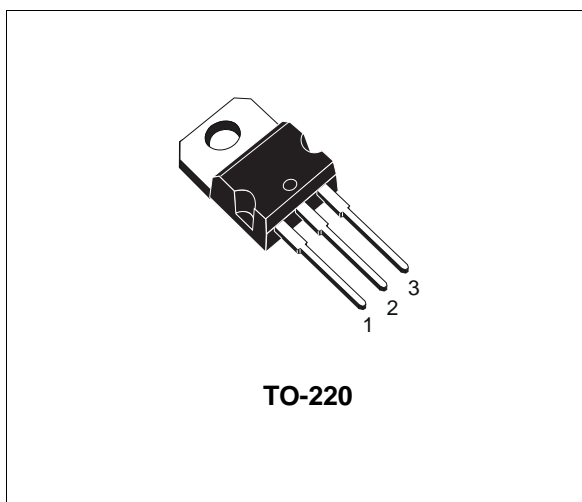


SILICON NPN SWITCHING TRANSISTORS

■ SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The TIP47, TIP48, TIP49 and TIP50 are silicon multiepitaxial NPN planar transistors in Jedec TO-220 plastic package, intended for use in linear and switching applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit	
		NPN	TIP47	TIP48	TIP49		TIP50
V_{CBO}	Collector-Base Voltage ($I_E = 0$)		350	400	450	500	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)		250	300	350	400	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)		5				V
I_C	Collector Current		1				A
I_{CM}	Collector Peak Current		2				A
I_B	Base Current		0.6				A
P_{tot}	Total Dissipation at $T_{case} \leq 25\text{ }^\circ\text{C}$ $T_{amb} \leq 25\text{ }^\circ\text{C}$		40				W
			2				W
T_{stg}	Storage Temperature		-65 to 150				$^\circ\text{C}$
T_j	Max. Operating Junction Temperature		150				$^\circ\text{C}$

TIP47/TIP48/TIP49/TIP50

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3.125	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W

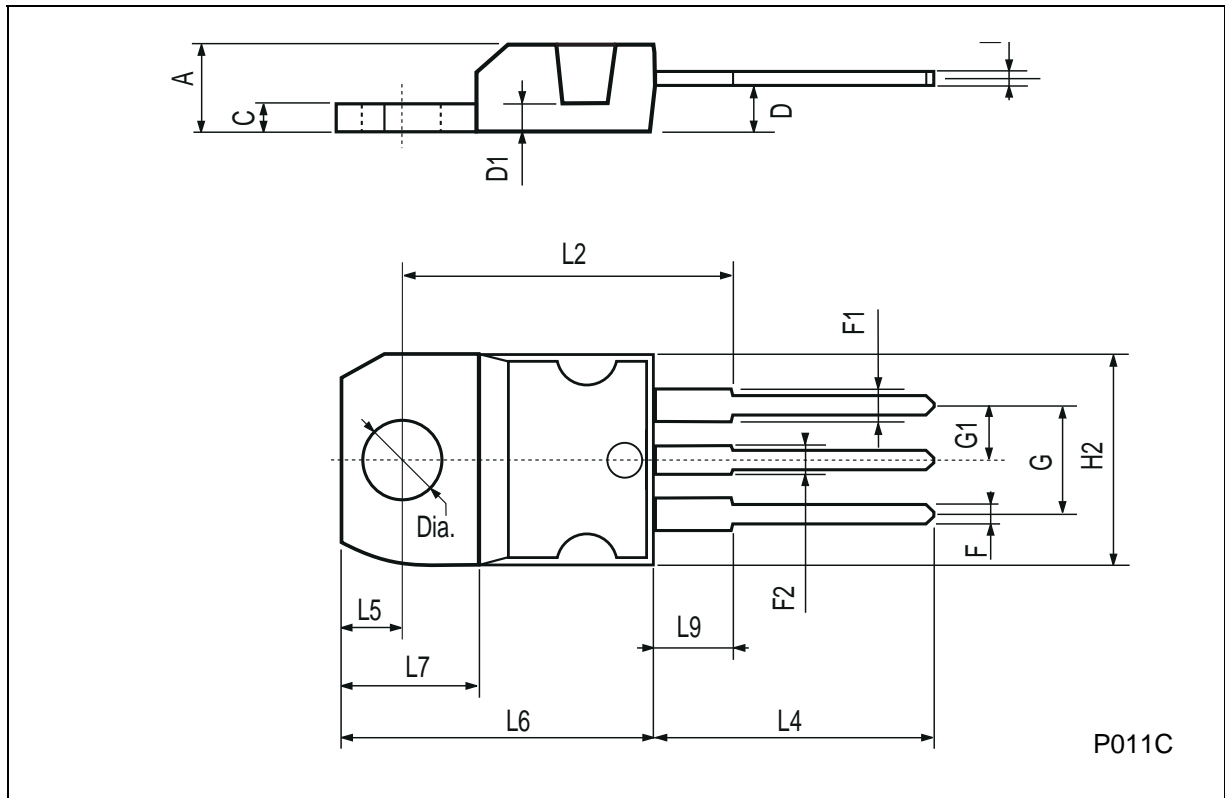
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	for TIP47 V _{CE} = 350 V for TIP48 V _{CE} = 400 V for TIP49 V _{CE} = 450 V for TIP50 V _{CE} = 500 V			1	mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	for TIP47 V _{CE} = 150 V for TIP48 V _{CE} = 200 V for TIP49 V _{CE} = 250 V for TIP50 V _{CE} = 300 V			1	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP47 for TIP48 for TIP49 for TIP50	250 300 350 400			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 1 A I _B = 0.2 A			1	V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 1 A V _{CE} = 10 V			1.5	V
h _{FE} *	DC Current Gain	I _C = 0.3 A V _{CE} = 10 V I _C = 1 A V _{CE} = 10 V	30 10		150	
f _T	Transition Frequency	V _{CE} = 10 V I _C = 0.2 A f = 2 MHz	10			MHz
h _{fe}	Small Signal Current Gain	V _{CE} = 10 V I _C = 0.2 A f = 1 MHz	25			

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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